

Nch 100V 20A Power MOSFET

V_{DSS}	100V
R _{DS(on)} (Max.)	46m $Ω$
I _D	20A
P_D	20W

Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating; RoHS compliant
- 6) 100% Avalanche tested

Application

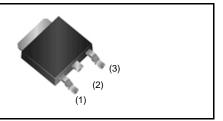
Switching Power Supply

Automotive Motor Drive

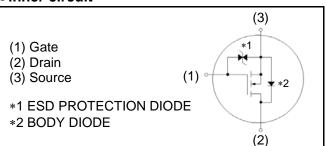
Automotive Solenoid Drive

Outline

CPT3 (SC-63) <SOT-428>



●Inner circuit



Packaging specifications

	Packaging	Taping
	Reel size (mm)	330
Typo	Tape width (mm)	16
Туре	Basic ordering unit (pcs)	2,500
	Taping code	TL
	Marking	201N10

• Absolute maximum ratings($T_a = 25$ °C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	100	V
Continuous drain current	T _c = 25°C	I _D ^{*1}	±20	А
	T _c = 100°C	I _D ^{*1}	±10	А
Pulsed drain current		I _{D,pulse} *2	±80	А
Gate - Source voltage		V_{GSS}	±20	V
Avalanche energy, single pulse		E _{AS} *3	14.6	mJ
Avalanche current		I _{AR} *3	10	А
T _c = 25°C		P_{D}	20	W
Power dissipation $T_a = 25^{\circ}C$		P_D	0.85	W
Junction temperature		T _j	150	°C
Range of storage temperature		T_{stg}	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
raiametei	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - ambient	R _{thJC}	-	-	6.25	°C/W

●Electrical characteristics(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	100	ı	ı	V
		$V_{DS} = 100V, V_{GS} = 0V$			1	
Zara gata valtaga drain augrent		$T_j = 25^{\circ}C$	-	-	1	μΑ
Zero gate voltage drain current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V			100	
		T _j = 125°C	-			
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μΑ
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V$, $I_D = 1mA$	1.0	-	2.5	V
		$V_{GS} = 10V, I_D = 20A$	-	33	46	
Static drain - source on - state resistance	D *4	$V_{GS} = 4.0V, I_D = 20A$	-	36	50	~~ ()
	R _{DS(on)}	$V_{GS} = 10V, I_D = 20A$		60	0.4	mΩ
		T _j = 125°C	-	60 84	84	
Forward transfer admittance	g _{fs}	$V_{DS} = 10V, I_D = 20A$	15	30	-	S

●Electrical characteristics(T_a = 25°C)

Parameter	Symbol	Conditions		Unit		
r ai ai ii e lei	Syllibol	nboi Conditions -		Тур.	Max.	Offic
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	2100	-	
Output capacitance	C _{oss}	V _{DS} = 25V	-	180	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	120	-	
Turn - on delay time	t _{d(on)} *4	$V_{DD} \simeq 50V, V_{GS} = 10V$	-	100	-	
Rise time	t _r *4	I _D = 10A	-	35	-	no
Turn - off delay time	t _{d(off)} *4	$R_L = 12\Omega$	-	150	-	ns
Fall time	t _f *4	$R_G = 10\Omega$	-	100	-	

• Gate Charge characteristics ($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol Conditions -		Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*4}	$V_{DD} \simeq 50V$	-	55	-	
Gate - Source charge	Q _{gs} *4	I _D = 20A	-	5.5	-	nC
Gate - Drain charge	${\sf Q_{gd}}^{^{*4}}$	V _{GS} = 10V	-	12.5	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 30V$, $I_D = 20A$	-	2.7	-	V

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Doromotor	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous source current	l _S *1	T _c = 25°C	-	-	14	А
Pulsed source current	I _{SM} *2	1 c = 25 C	-	-	80	Α
Forward voltage	V_{SD}^{*4}	$V_{GS} = 0V, I_{S} = 20A$	-	-	1.5	V
Reverse recovery time	t _{rr} *4	I _S = 20A	-	65	-	ns
Reverse recovery charge	Q _{rr} *4	di/dt = 100A/μs	-	144	-	μС

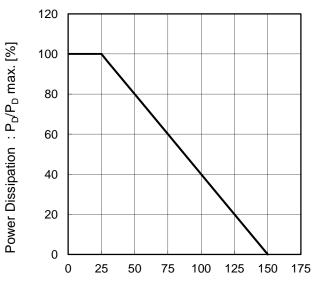
^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} L \simeq 100 μ H, V_{DD} = 50V, Rg = 10 Ω , starting T_j = 25°C

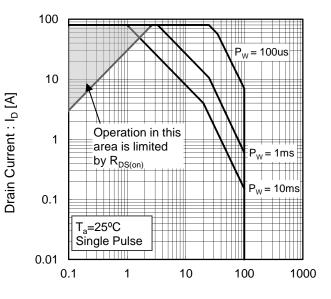
^{*4} Pulsed

Fig.1 Power Dissipation Derating Curve



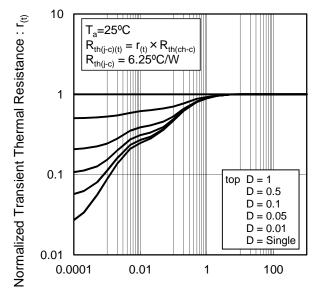
Junction Temperature : T_i [°C]

Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width : $P_W[s]$

Fig.4 Avalanche Current vs Inductive Load

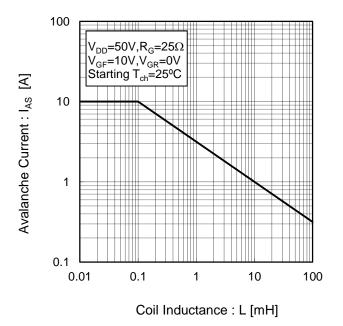
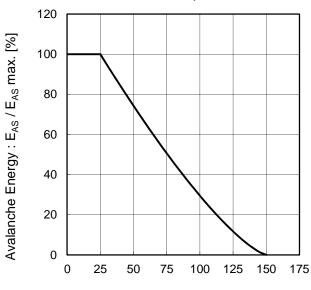
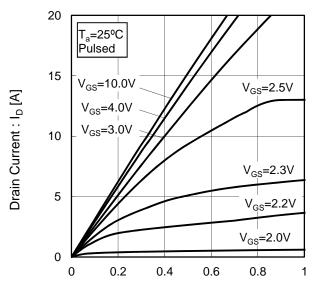


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature



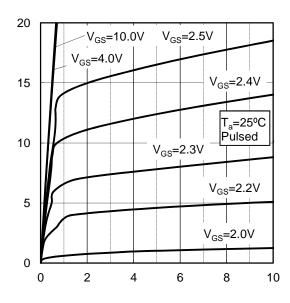
Junction Temperature : T_i [°C]

Fig.6 Typical Output Characteristics(I)



Drain - Source Voltage : V_{DS} [V]

Fig.7 Typical Output Characteristics(II)

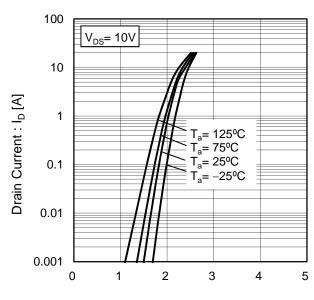


Drain - Source Voltage : V_{DS} [V]

Drain Current : I_D [A]

Fig.8 Breakdown Voltage vs. Junction Temperature 120 Normarize Drain - Source Breakdown Voltage $V_{GS} = 0V$ 115 $I_D = 1 \text{mA}$ 110 105 100 95 90 85 80 -50 0 50 100 150 Junction Temperature : T_i [°C]

Fig.9 Typical Transfer Characteristics



Gate - Source Voltage : V_{GS} [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature

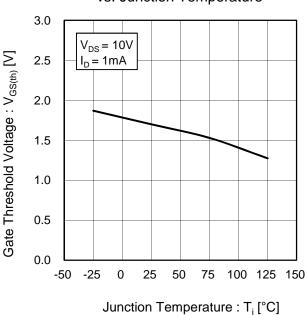
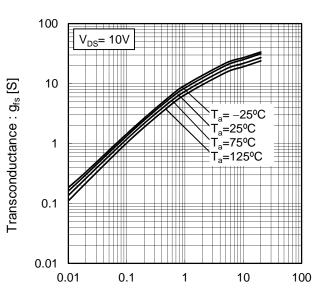


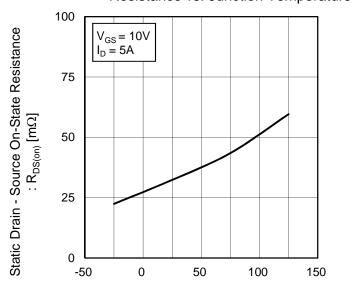
Fig.11 Transconductance vs. Drain Current



Drain Current : I_D [A]

Fig.12 Static Drain - Source On - State Fig.13 Static Drain - Source On - State Resistance vs. Gate Source Voltage Resistance vs. Drain Current(I) 100 100 Static Drain - Source On-State Resistance T_a=25°C T_a=25°C Static Drain - Source On-State Resistance 75 V_{GS}= 4.5V $I_D = 10A$ V_{GS}= 4.0V $: R_{\text{DS(on)}} \left[\text{m}\Omega\right]$ $:R_{\text{DS(on)}}\left[\text{m}\Omega \right]$ $I_{D} = 20A$ 50 25 0 10 0 5 10 15 0.01 0.1 1 10 100 Gate - Source Voltage : V_{GS} [V] Drain Current : I_D [A]

Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



Junction Temperature : T_j [°C]

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II) 1000 Static Drain - Source On-State Resistance $V_{GS} = 10V$ $:R_{\text{DS(on)}}\left[\text{m}\Omega \right]$ 100 10 0.01 0.1 1 10 100 Drain Current : I_D [A]

Fig.16 Static Drain-Source On-State Resistance vs. Drain Current(III) 1000 Static Drain - Source On-State Resistance V_{GS}= 4.5V $:R_{\mathsf{DS}(\mathsf{on})}\left[\mathsf{m}\Omega \right]$ 100 10 0.01 0.1 10 100 Drain Current: I_D [A]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV) 1000 Static Drain - Source On-State Resistance $V_{GS} = 4.0V$ $: R_{DS(on)} \left[m\Omega
ight]$ 100 10 0.01 0.1 1 10 100 Drain Current: ID [A]

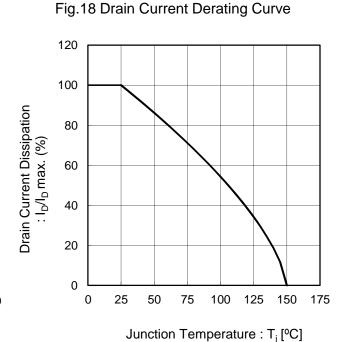
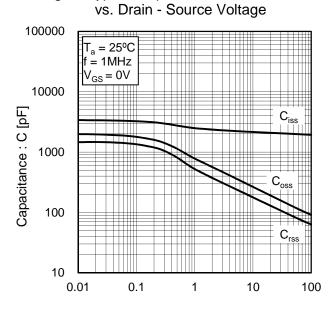
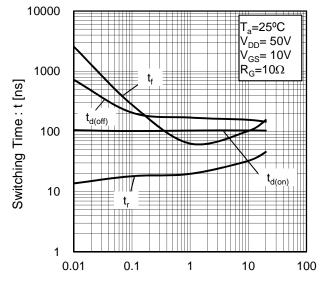


Fig.19 Typical Capacitance



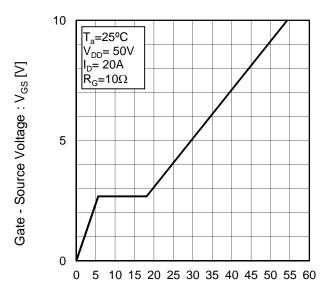
Drain - Source Voltage : V_{DS} [V]

Fig.20 Switching Characteristics



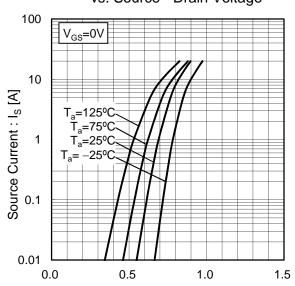
Drain Current : I_D [A]

Fig.21 Dynamic Input Characteristics

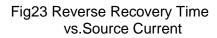


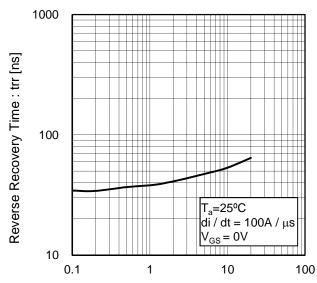
Total Gate Charge : Q_q [nC]

Fig.22 Source Current vs. Source - Drain Voltage



Source-Drain Voltage: V_{SD} [V]





Source Current : I_S [A]

●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

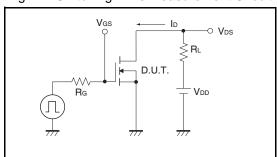


Fig.2-1 Gate Charge Measurement Circuit

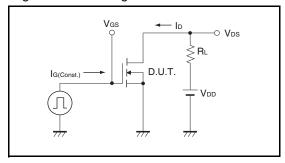


Fig.3-1 Avalanche Measurement Circuit

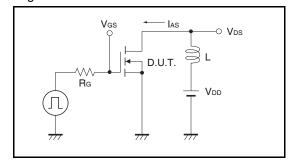


Fig.1-2 Switching Waveforms

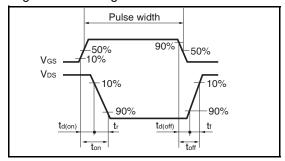


Fig.2-2 Gate Charge Waveform

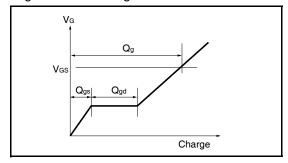
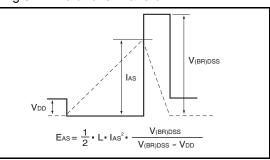
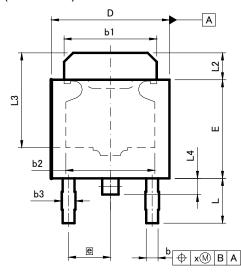


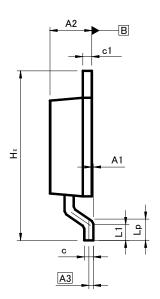
Fig.3-2 Avalanche Waveform

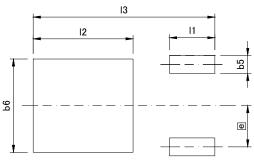


●Dimensions (Unit : mm)









DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
A1	0.00	0.15	0	0.006	
A2	2.20	2.50	0.087	0.098	
A3	0.:	25	0.	01	
b	0.55	0.75	0.022	0.03	
b1	5.00	5.30	0.197	0.209	
b2	5.0	00	0.	20	
b3	0.	75	0.	03	
С	0.40	0.60	0.016	0.024	
c1	0.40	0.60	0.016	0.024	
D	6.30	6.70	0.248	0.264	
Е	5.40	5.80	0.213	0.228	
е	2.	30	0.	09	
HE	9.00	10.00	0.354	0.394	
L	2.20	2.80	0.087	0.11	
L1	0.80	1.40	0.031	0.055	
L2	1.20	1.80	0.047	0.071	
L3	5.3	30	0.2	209	
L4	0.9	90	0.0	35	
Lp	1.00	1.60	0.039	0.063	
х		0.25	_	0.01	

	MILIMETERS		INCLIEC		
DIM	MILLIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b5	_	1.00	_	0.04	
b6	_	5.20	-	0.205	
11	-	2.50	-	0.098	
12	_	5.50	-	0.217	
13	_	10.00	_	0.394	

Dimension in mm/inches

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JAPAN	USA	EU	CHINA
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CLASSIV	CLASSIII	CLASSⅢ	CLASSIII

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 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation (Pd) depending on Ambient temperature (Ta). When used in sealed area, confirm the actual ambient temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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